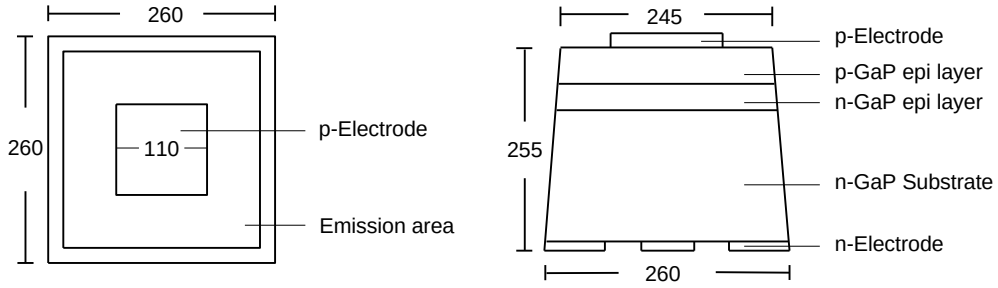
Features :

- GaP Epi Wafer

Typical Applications :

- Lamp
- SMD
- Display

Outline Dimensions : (Unit: um)



Physical Structure :

Chip dimension	Chip size	260 um x260 um
	Thickness	255 um
	Emission area	245 um
	Bonding pad	110um
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

Electro-Optical Characteristics : (Ta = 25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F = 20 mA	1.80	2.20	2.60	V
Reverse Current	I_R	V_R = 5 V	-	-	10	uA
Wavelength	λ_P	I_F = 20 mA	-	565	-	nm
	Hue		-	570	-	
Spectral width at half height	△λ	I_F = 20 mA	-	26	-	nm
Luminous Intensity	I_V	I_F = 20 mA	4.0	7.0	-	mcd

Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

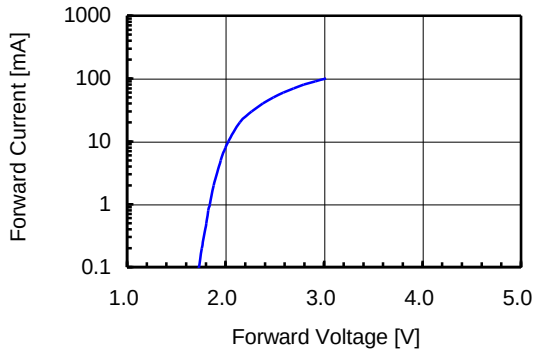


Fig 2. Relative Intensity vs. Forward Current

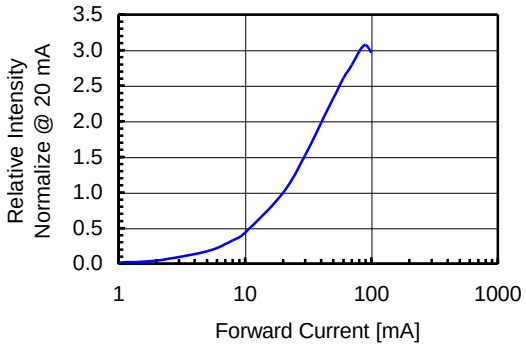


Fig 3. Forward Voltage vs. Temperature

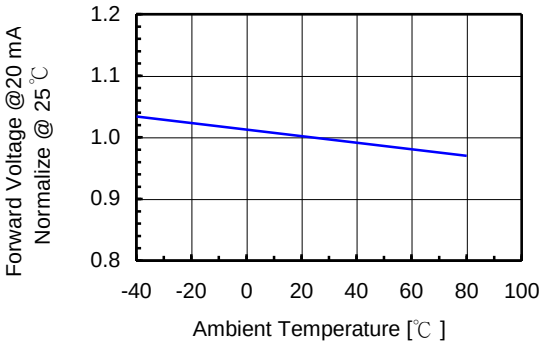


Fig4. Relative Intensity vs. Temperature

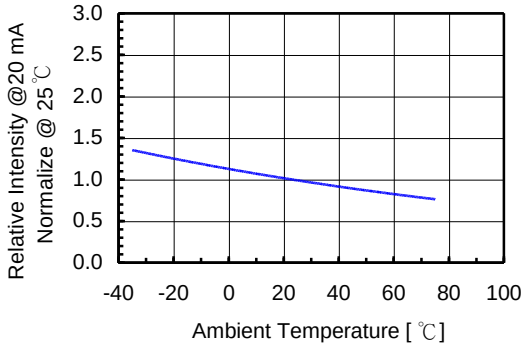


Fig 5. Relative Intensity vs. Wavelength